

EL 4831664

DECLARATION OF SOLE INVENTOR FOR PATENT APPLICATION

As the below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated
below next to my name.

I believe I am the original, first and sole inventor of the subject
matter which is claimed and for which a patent is sought on the
invention entitled: **Field Effect Transistors, Integrated Circuitry,
Methods Of Forming Field Effect Transistor Gates, And Methods Of
Forming Integrated Circuitry**, the specification of which is attached
hereto.

I hereby state that I have reviewed and understand the contents
of the above-identified specification, including the claims.

I acknowledge the duty to disclose information known to me to
be material to patentability as defined in Title 37, Code of Federal
Regulations §1.56.

PRIOR FOREIGN APPLICATIONS:

I hereby state that no applications for foreign patents or inventor's
certificates have been filed prior to the date of execution of this
declaration.

I hereby declare that all statements made herein of my own
knowledge are true and that all statements made on information and
belief are believed to be true; and further that these statements were
made with the knowledge that willful false statements and the like so
made are punishable by fine or imprisonment, or both, under

1 Section 1001 of Title 18 of the United States Code and that such willful
2 false statement may jeopardize the validity of the application or any
3 patent issued therefrom.

4 * * * * *

5 Full name of sole inventor: **Charles H. Dennison**

6 Inventor's Signature: Carl H Dennison

7 Date: 8-19-98

8 Residence: **Meridian, Idaho**

9 Citizenship: **U.S.A.**

10 Post Office Address: **7315 Rhine Ave.**
11 **Meridian, ID 83642**

12

13

14

15

16

17

18

19

20

21

22

23

24